

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Please amend claim 1 and add new claims 24-26 as follows:

Claim 1 (Currently amended): A magnetic film comprising:

a magnetic alloy T-M-X wherein T is at least 90 atomic percent of one element selected from the group consisting of Fe, Co, and Ni, M is selected from the group consisting of B, Al, Si, P, Ti, V, Cr, Cu, Ga, Ge, Zr, Nb, Mo, Ru, In, Sn, Hf, and Ta, and X is selected from the group consisting of N, O, and C; and

at least a single nanolamination of ~~a~~ an amorphous material selected from the group consisting of Al₂O₃, SiO₂, ZrO₂, yttria-stabilized ZrO₂, TiO₂, HfO₂, Ta₂O₅, Si₃N₄, AlN, B₄C, SiC[,] and Si₄N₄, ~~Ta, Zr, and Hf~~; wherein said nanolamination is a discontinuous layer embedded within the magnetic alloy.

Claim 2 (Original): A magnetic film according to claim 1, wherein T is Fe and X is N.

Claim 3 (Original): A magnetic film according to claim 1, wherein the nanolamination has a thickness of approximately 0.4 to 1.7 Å.

Claims 4-23 (Withdrawn)

Claim 24 (New): A magnetic film structure comprising:

a plurality of repetitions of magnetic layers alternately laminated with relatively thinner nonmagnetic layers, wherein said magnetic layers comprise:

a magnetic alloy T-M-X wherein T is at least 90 atomic percent of one element selected from the group consisting of Fe, Co, and Ni, M is selected from the group consisting of B, Al, Si, P, Ti, V, Cr, Cu, Ga, Ge, Zr, Nb, Mo, Ru, In, Sn, Hf, and Ta, and X is selected from the group consisting of N, O, and C; and at least a single nanolamination of a material selected from the group consisting of Al_2O_3 , SiO_2 , ZrO_2 , yttria-stabilized ZrO_2 , TiO_2 , HfO_2 , Ta_2O_5 , Si_3N_4 , AlN , B_4C , SiC , Si_4N_4 , Ta, Zr, and Hf, wherein said nanolamination is a discontinuous layer; and

said nonmagnetic layers are selected from the group consisting of Al_2O_3 , SiO_2 , ZrO_2 , yttria-stabilized ZrO_2 , TiO_2 , HfO_2 , Ta_2O_5 , Si_3N_4 , AlN , B_4C , SiC , Si_4N_4 , Ta, Zr, and Hf.

Claim 25 (New): A magnetic film structure according to claim 24, wherein T is Fe and X is N.

Claim 26 (New): A magnetic film structure according to claim 24, wherein the nanolamination has a thickness of approximately 0.4 to 1.7 Å.